

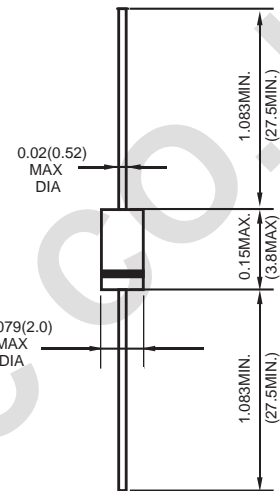
### FEATURES

- For general purpose applications
- Metal-on-silicon junction Schottky barrier which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications
- These diodes are also available in the Mini-MELF case with type designation LL6263, in the Micro-MELF case with type designation MCL6263

### MECHANICAL DATA

- **Case:** DO-35 Glass CASE
- **Polarity:** Color band denotes cathode end
- **Weight:** Approx. 0.13gram

DO-35



Dimensions in inches and (millimeters)

### ABSOLUTE RATINGS(LIMITING VALUES)

	SYMBOLS	VALUE	UNITS
Peak Reverse Voltage	$V_{RRM}$	60	V
Power Dissipation (infinite Heat Sink)	$P_{tot}$	400	mW
Maximum Single cycle surge 10 $\mu$ s square wave	$I_{FSM}$	2.0	A
Junction Temperature	$T_J$	125	$^{\circ}$ C
Storage Temperature Range	$T_{STG}$	-55 to +150	$^{\circ}$ C

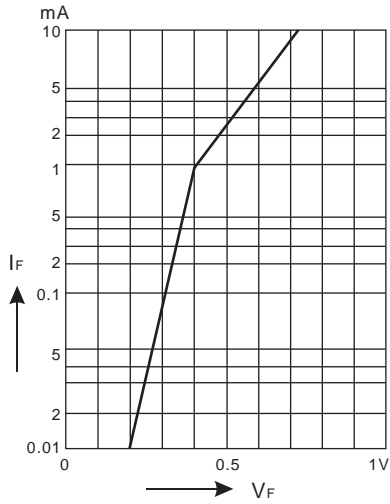
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

### ELECTRICAL CHARACTERISTICS

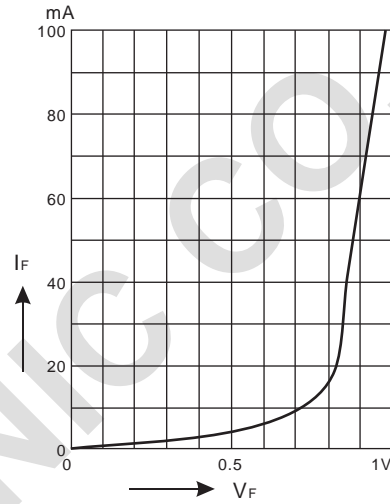
(Ratings at 25 $^{\circ}$ C ambient temperature unless otherwise specified)

	SYMBOLS	Min.	TYP.	MAX.	UNITS
Reverse Breakover Voltage at $I_R=10\mu A$	$V_R$	60			V
Leakage Current at $V_R=50V$	$I_R$			200	nA
Forward voltage drop at $I_F=1mA$ $I_F=15mA$	$V_F$			0.41 1.0	V
Junction Capacitance at $V_R=0V, f=1MHz$	$C_J$			2.0	pF
Reverse Recovery time at $I_F=I_R=5mA$ , recover to 0.1 $I_R$	$T_{rr}$			1	ns
Thermal resistance	$R_{\theta JA}$			0.3	K/W

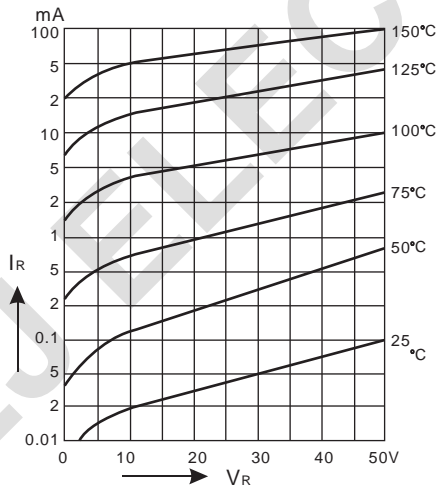
**Fig.1 Typical variation of forward. Current vs forward.voltage for primary conduction through the Schottky barrier**



**Fig.2 Typical forward conduction curve of combination Schottky barrier and PN iunction guard ring**



**Fig.3 Typical variation of reverse current at various temperatures**



**Fig.4 Typical variation curve as a function of reverse voltage**

